



DMTH43M8LFGQ

D

S Equivalent Circuit

40V 175°C N-CHANNEL ENHANCEMENT MODE MOSFET PowerDI3333-8

Product Summary

BV _{DSS}	R _{DS(ON)} Max	I _D Max (Note 10) T _C = +25°C
	3.0mΩ @ V _{GS} = 10V	100A
40V	5.0mΩ @ V _{GS} = 5V	93A

Description and Applications

This MOSFET is designed to meet the stringent requirements of automotive applications. It is qualified to AEC-Q101, supported by a PPAP and is ideal for use in:

- Motor Control
- **DC-DC** Converters
- **Power Management**

Features and Benefits

- Rated to +175°C Ideal for High Ambient Temperature Environments
- 100% Unclamped Inductive Switching, Test in Production -Ensures More Reliable and Robust End Application
- Low R_{DS(ON)} Ensures On-State Losses are Minimized
- Excellent Q_{GD} × R_{DS(ON)} Product (FOM)
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability
- PPAP Capable (Note 4)

Mechanical Data

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- Case: PowerDl[®]3333-8
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0

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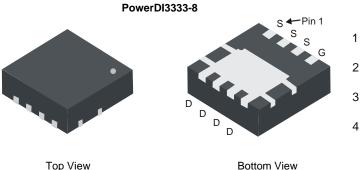
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- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Finish Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 @3
- Weight: 0.008 grams (Approximate)

Top View



Top View

Ordering Information (Note 5)

Part Number	Case	Packaging
DMTH43M8LFGQ-7	PowerDI3333-8	2,000/Tape & Reel
DMTH43M8LFGQ-13	PowerDI3333-8	3,000/Tape & Reel

Notes:

1. EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant. All applicable RoHS exemptions applied.

2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.

3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

4. Automotive products are AEC-Q101 gualified and are PPAP capable. Refer to https://www.diodes.com/guality/.

5. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information



HK8 = Product Type Marking Code YYWW = Date Code Marking YY = Last Two Digits of Year (ex: 19 = 2019) WW = Week Code (01 to 53)



Maximum Ratings ($@T_C = +25^{\circ}C$, unless otherwise specified.)

Characteristic	Symbol	Value	Unit	
Drain-Source Voltage	V _{DSS}	40	V	
Gate-Source Voltage	V _{GSS}	±20	V	
Continuous Drain Current (Note 7) (Note 10) V_{GS} = 10V	T _C = +25°C T _C = +100°C	ID	100 85	А
Continuous Drain Current (Note 6) $V_{GS} = 10V$	T _A = +25°C T _A = +100°C	ID	24.0 16.9	А
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)		I _{DM}	400	А
Maximum Continuous Body Diode Forward Current (Note 7) (N	Is	100	А	
Pulsed Body Diode Forward Current (10µs Pulse, Duty Cycle =	I _{SM}	400	А	
Avalanche Current, L = 1mH	I _{AS}	18.2	А	
Avalanche Energy, L = 1mH	E _{AS}	165	mJ	

Thermal Characteristics

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 6)	T _A = +25°C	PD	2.62	W
Thermal Resistance, Junction to Ambient (Note 6)	R _{θJA}	57.8	°C/W	
Total Power Dissipation (Note 7) $T_{\rm C} = +25^{\circ}{\rm C}$		PD	65.2	W
Thermal Resistance, Junction to Case (Note 7)	R _{θJC}	2.3	°C/W	
Operating and Storage Temperature Range	TJ, TSTG	-55 to +175	°C	

Electrical Characteristics (@T_J = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	True	Max	11	Toot Condition
Characteristic OFF CHARACTERISTICS (Note 8)		Min	Тур	Max	Unit	Test Condition
		40			V	
Drain-Source Breakdown Voltage		40				$V_{GS} = 0V, I_D = 1mA$
Zero Gate Voltage Drain Current		_		1	μA	$V_{DS} = 32V, V_{GS} = 0V$
Gate-Source Leakage	I _{GSS}			±100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$
ON CHARACTERISTICS (Note 8)				r .		
Gate Threshold Voltage	V _{GS(TH)}	1	1.5	2.5	V	$V_{DS} = V_{GS}, I_D = 250 \mu A$
Static Drain-Source On-Resistance	Proven		2.3	3.0		$V_{GS} = 10V, I_D = 20A$
	R _{DS(ON)}	—	3.4	5.0	mΩ	$V_{GS} = 5V, I_D = 15A$
Statia Drain Source On Begistenes (T. 175%C) (Note 0)	D	—		6.0	mΩ	$V_{GS} = 10V, I_D = 20A$
Static Drain-Source On-Resistance ($T_J = +175^{\circ}C$) (Note 9)	R _{DS(ON)}	_	_	9.0		V _{GS} = 5V, I _D = 15A
Diode Forward Voltage	V _{SD}		0.8	1.0	V	$V_{GS} = 0V, I_{S} = 20A$
DYNAMIC CHARACTERISTICS (Note 9)						
Input Capacitance	Ciss	_	2798	_		$V_{DS} = 20V, V_{GS} = 0V,$ f = 1MHz
Output Capacitance	Coss	_	904	_	pF	
Reverse Transfer Capacitance	Crss	_	88	—		
Gate Resistance	R _G	—	2.44	—	Ω	$V_{DS} = 0V, V_{GS} = 0V, f = 1MHz$
Total Gate Charge (V _{GS} = 10V)	Q _G	_	40.1	—		
Gate-Source Charge	Q _{GS}		5.2	_	nC	V _{DS} = 20V, I _D = 20A, V _{GS} = 10V
Gate-Drain Charge	Q _{GD}		8.8	_		
Turn-On Delay Time	t _{D(ON)}		5.16	—		$V_{DD} = 20V, V_{GS} = 10V,$ $R_G = 1.6\Omega, I_D = 20A$
Turn-On Rise Time	t _R		10.7	_		
Turn-Off Delay Time	t _{D(OFF)}	_	24.6	—	ns	
Turn-Off Fall Time	t _F	_	12.4	—		
Body Diode Reverse Recovery Time	t _{RR}	_	32.6	_	ns	
Body Diode Reverse Recovery Charge	Q _{RR}	_	26.6	—	nC	$I_F = 15A$, di/dt = 100A/µs

 6. Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1-inch square copper plate.
 7. Thermal resistance from junction to soldering point (on the exposed drain pad).
 8. Short duration pulse test used to minimize self-heating effect.
 9. Guaranteed by design. Not subject to product testing.
 10. Package limit. Notes:



30.0 = 10.0V 25.0 5.0V $V_{GS} = 3.2V$ _{GS} = 4.5V I_D, DRAIN CURRENT (A) 20.0 _{GS} = 4.0V $V_{GS} = 3.5V$ 15.0 $V_{GS} = 3.0V$ 10.0 $V_{GS} = 2.8V$ 5.0 $V_{GS} = 2.5V$ 0.0 2.5 0 0.5 1.5 2 3 1 V_{DS}, DRAIN-SOURCE VOLTAGE (V) Figure 1. Typical Output Characteristic 4.0 R_{DS(ON)}, DRAIN-SOURCE ON-RESISTANCE 3.8 3.6 $V_{GS} = 5.0V$ 3.4 3.2 3.0 (Dm) 2.8 2.6 2.4 $V_{GS} = 10V$ 2.2 2.0 1.8 1.6 1.4 0 5 10 15 20 25 30 I_D, DRAIN-SOURCE CURRENT (A) Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage 5 R_{DS(ON)}, DRAIN-SOURCE ON-RESISTANCE $V_{GS} = 10V$ 4.5 T_J=175℃ 4 T_I= 150℃ T_**= 125**℃ 3.5 T_J=85℃ 3 (MD) 2.5 T_J=25℃ 2 T_**= -55°**℃ 1.5 1 0.5 5 0 10 15 20 25 30 I_D, DRAIN CURRENT (A)

Figure 5. Typical On-Resistance vs. Drain Current and Temperature

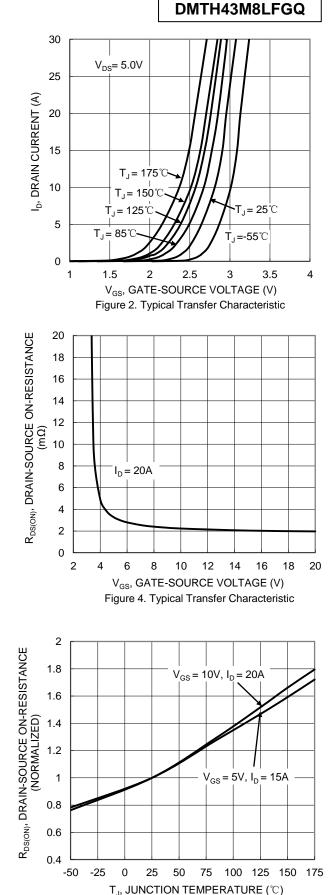


Figure 6. On-Resistance Variation with Temperature



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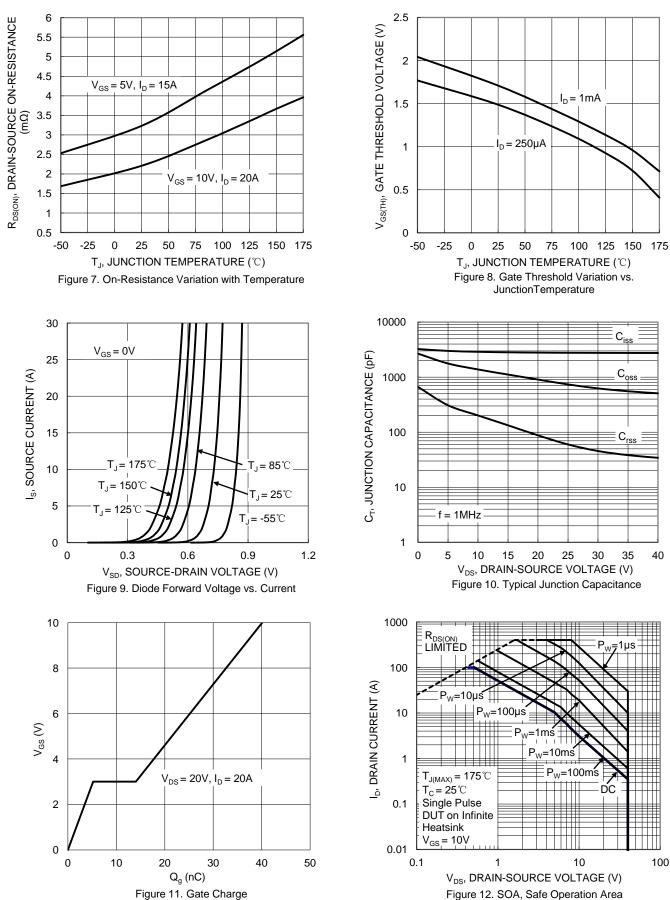
C_{iss}

Coss

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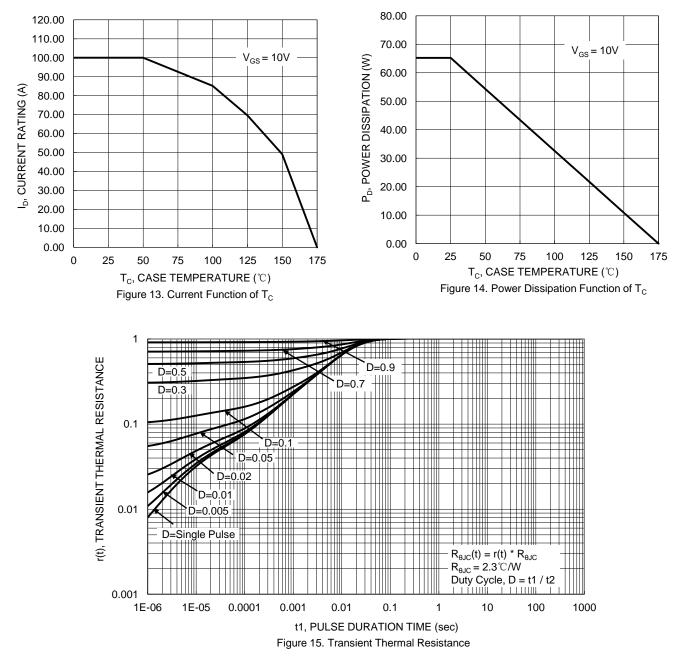


100

DC



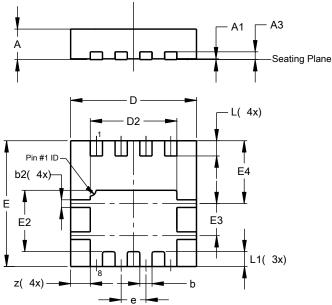
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Package Outline Dimensions

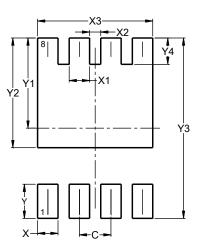
Please see http://www.diodes.com/package-outlines.html for the latest version.



	PowerDI3333-8					
Dim	Min	Max	Тур			
Α	0.75	0.85	0.80			
A1	0.00	0.05	0.02			
A3	-	-	0.203			
b	0.27	0.37	0.32			
b2	0.15	0.25	0.20			
D	3.25	3.35	3.30			
D2	2.22	2.32	2.27			
Ε	3.25	3.35	3.30			
E2	1.56	1.66	1.61			
E3	0.79	0.89	0.84			
E4	1.60	1.70	1.65			
е	_	_	0.65			
L	0.35	0.45	0.40			
L1	_	_	0.39			
z	_	-	0.515			
All I	All Dimensions in mm					

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.



PowerDI3333-8

Dimensions	Value (in mm)		
С	0.650		
Х	0.420		
X1	0.420		
X2	0.230		
X3	2.370		
Y	0.700		
Y1	1.850		
Y2	2.250		
Y3	3.700		
Y4	0.540		

PowerDI3333-8



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